

Docket No.: Z&PINFP10306

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231, on the date indicated below.

By: 

Date: September 10, 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Annette Snger
Applic. No. : 10/034,053
Filed : December 20, 2001
Title : Process for the Deposition of Thin Layers by Chemical Vapor Deposition
Art Unit : 1763

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. 1.97(C)(1)

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 3,334,103 (Feldman et al.), dated August 1, 1967;

United States Patent No. 5,589,425 (Hoshino et al.), dated December 31, 1996;

United States Patent No. 5,637,351 (O'Neal et al.), dated June 10, 1997;

European Patent Application EP 1 108 468 A1 (Won-Sun), dated June 20, 2001;

European Patent Application EP 1 158 070 A1 (Lakhotkin et al.), dated November 28, 2001;

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J.G. Martin et al.: "Mechanisms of silicone dioxide deposition from the low pressure chemical vapor deposition of diethylsilane/oxygen mixtures", Journal of the Electrochemical Society, Vol. 142, November 1995, No. 11, pp. 3873-3880, INSPEC Abstract;

International Search Report dated July 2, 2002.

In accordance with 37 C.F.R. 1.97(e) the undersigned herewith states that each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

In accordance with 37 C.F.R. 1.97 (c) (1), consideration of this Information Disclosure Statement is requested.

Respectfully submitted,



For Applicant

Mark P. Weichselbaum
Reg. No. 43,248

Date: September 10, 2002

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/bmb



FORM PTO-1449 (SUBSTITUTE)				Attorney Docket No.: Z&PINFP10306				Applic. No. 10/034,053	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Applicant Annette Snger					
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Filing Date December 20, 2001		Group Art Unit 1763			
U.S. PATENT DOCUMENTS									
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE		
	A	3,334,103	08/01/67	Feldman et al.					
	B	5,589,425	12/31/96	Hoshino et al.					
	C	5,637,351	06/10/97	O'Neal et al.					
	D								
	E								
	F								
	G								
	H								
	I								
FOREIGN PATENT DOCUMENT									
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO		
	J	1 108 468 A1	06/20/01	Europe			X		
	K	1 158 070 A1	11/28/01	Europe			X		
	L								
	M								
	N								
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)									
	O	J.G. Martin et al.: "Mechanisms of silicone dioxide deposition from the low pressure chemical vapor deposition of diethylsilane/oxygen mixtures", Journal of the Electrochemical Society, Vol. 142, November 1995, No. 11, pp. 3873-3880, INSPEC Abstract							
	P								
EXAMINER				DATE CONSIDERED					
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

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